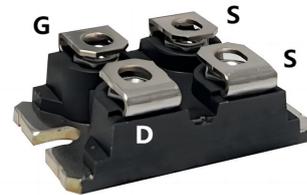


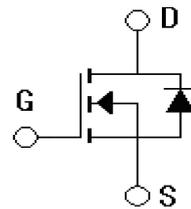
Features

- Low $R_{DS(on)}$
- Fast switching
- 100% avalanche tested
- Low package inductance
- Low intrinsic Rectifier
- RoHS Compliant



Applications

- DC-DC converters
- Battery chargers
- Switched-mode and resonant-mode power supplies
- DC chopper
- Temperature and lighting controls
- Linear current regulators



Absolute Ratings ($T_c=25^\circ\text{C}$)

Parameter	Symbol	Value	Unit	
Drain-Source Voltage	V_{DSS}	70	V	
Drain Current -continuous	I_D	$T=25^\circ\text{C}$	340	A
		$T=100^\circ\text{C}$	170	A
Drain Current - pulse (note 1)	I_{DM}	1360	A	
Gate-Source Voltage	V_{GSS}	± 30	V	
Single Pulsed Avalanche Energy (note 2)	E_{AS}	4000	mJ	
Avalanche Current (note 1)	I_{AR}	200	A	
Repetitive Avalanche Current (note 1)	E_{AR}	64	mJ	
Peak Diode Recovery dv/dt (note 3)	dv/dt	10	V/ns	
Power Dissipation	PD $TC=25^\circ\text{C}$	694	W	
	-Derate above 25°C	2.86	W/ $^\circ\text{C}$	
Operating and Storage Temperature Range	T_j, T_{STG}	$-55 \sim +150$	$^\circ\text{C}$	
Maximum Lead Temperature for Soldering Purposes	T_L	300	$^\circ\text{C}$	

Isolation voltage for terminal to case ($I_{ISOL} \leq 1\text{mA}, t=1\text{s}, \text{DC}$)	V_{ISO}	3000	V
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Electrical Characteristics($T_{CASE}=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Tests conditions	Min	Type	Max	Units
Off-Characteristics						
Drain-Source Voltage	BV_{DSS}	$I_D=250\mu\text{A}, V_{GS}=0\text{V}$	70	-	-	V
Breakdown Voltage Temperature Coefficient	$\Delta BV_{DSS} / \Delta T_J$	$I_D=250\mu\text{A}$, referenced to 25°C	-	0.16	-	$\text{V}/^{\circ}\text{C}$
Drain cut-off current	I_{DSS}	$V_{DS}=70\text{V}, V_{GS}=0\text{V}$ $T_J=25^{\circ}\text{C}$	-	-	100	μA
		$V_{DS}=70\text{V}, T_J=125^{\circ}\text{C}$	-	-	2000	
Gate-body leakage current, forward	I_{GSSF}	$V_{DS}=0\text{V}, V_{GS}=30\text{V}$	-	-	500	nA
Gate-body leakage current, reverse	I_{GSSR}	$V_{DS}=0\text{V}, V_{GS}=-30\text{V}$	-	-	-500	nA
On-Characteristics						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu\text{A}$	2	-	4	V
Static Drain-Source On-Resistance	$R_{DS(ON)}$	$V_{GS}=10\text{V}, I_D=75\text{A}$ (note 3)	-	3.1	3.8	$\text{m}\Omega$
Forward Transconductance	g_{fs}	$V_{DS}=10\text{V}, I_D=75\text{A}$ (note 3)	-	116	-	S
Dynamic Characteristics						
Input capacitance	C_{iss}	$V_{DS}=25\text{V},$ $V_{GS}=0\text{V},$ $f=1.0\text{MHz}$	-	11000		pF
Output capacitance	C_{oss}		-	6700		pF
Reverse transfer capacitance	C_{rss}		-	3300		pF

Switching Characteristics						
Turn-On delay time	$t_{d(on)}$	$V_{DD}=35\text{V}, I_D=100\text{A},$ $R_G=25\Omega,$ $V_{GS}=10\text{V}(\text{note } 4,5)$	-	90	-	ns
Turn-On rise time	t_r		-	85	-	ns
Turn-Off delay time	$T_{d(off)}$		-	270	-	ns
Turn-Off Fall time	t_f		-	40	-	ns
Total Gate Charge	Q_g	$V_{DS}=50\text{V},$ $I_D=100\text{A},$ $V_{GS}=10\text{V}(\text{note } 4,5)$	-	450	-	nC
Gate-Source charge	Q_{gs}		-	72	-	nC
Gate-Drain charge	Q_{gd}		-	226	-	nC
Drain-Source Diode Characteristics and Maximum Ratings						

Drain-Source Diode Forward Voltage	V_{SD}	$V_{GS}=0V, I_S=30A$ (note 3)	-	0.81	1.2	V
Maximum Continuous Drain-Source Diode Forward Current		I_S	-	-	340	A
Maximum Pulsed Drain-Source Diode Forward Current		I_{SM}	-	-	1360	A
Reverse recovery time	t_{rr}	$V_{GS}=0V, I_F=50A$ $di_F/dt=100A/\mu s$ (note 3)	-	95	-	ns
Reverse recovery charge	Q_{rr}		-	1.23	-	μC

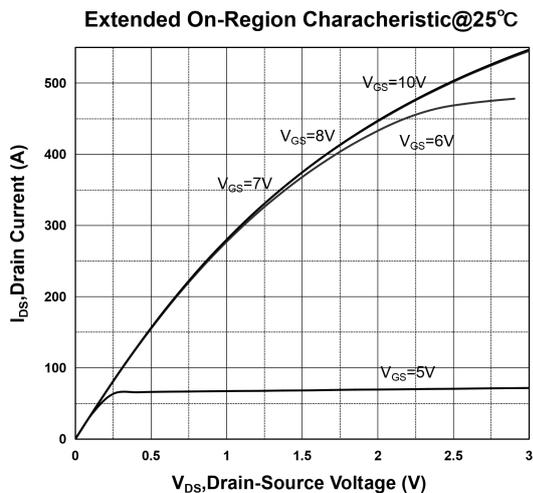
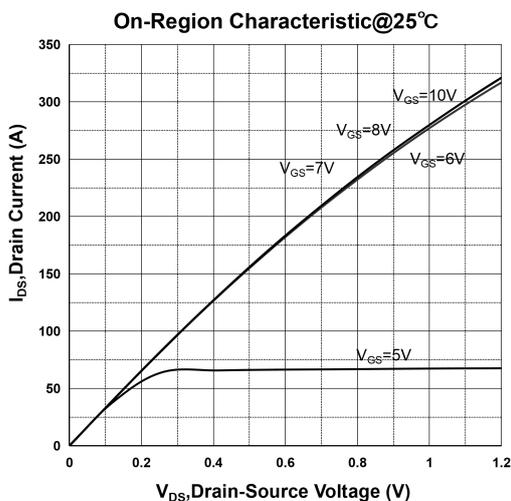
Thermal Characteristics

Parameter	Symbol	Value	Unit
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	0.18	$^{\circ}C/W$
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	40	$^{\circ}C/W$

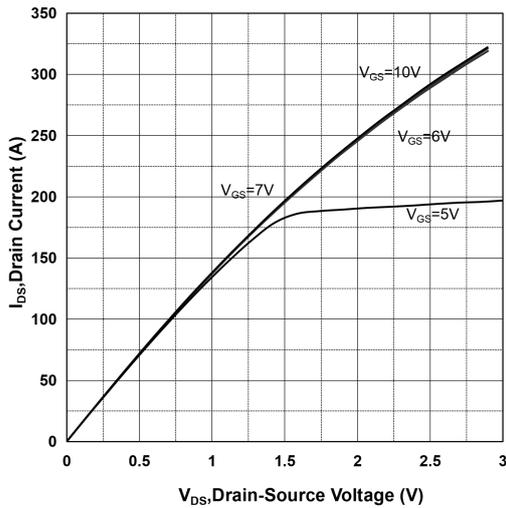
Notes:

- 1: Pulse width limited by maximum junction temperature
- 2: $L=0.5mH, I_{AS}=100A, V_{DD}=50V, R_G=25 \Omega$, Starting $T_J=25^{\circ}C$
- 3: $I_{SD} \leq 100A, di/dt \leq 300A/\mu s, V_{DD} \leq BV_{DSS}$, Starting $T_J=25^{\circ}C$
- 4: Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$
- 5: Essentially independent of operating temperature

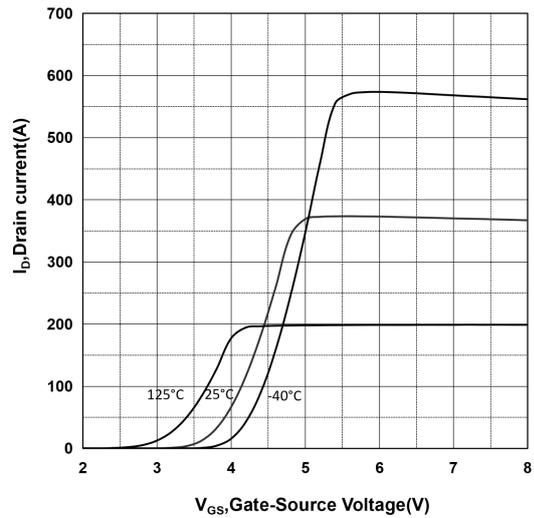
Electrical Characteristics



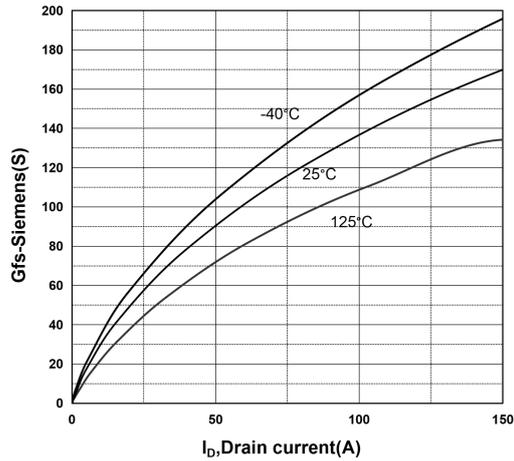
On-Region Characteristic@125°C



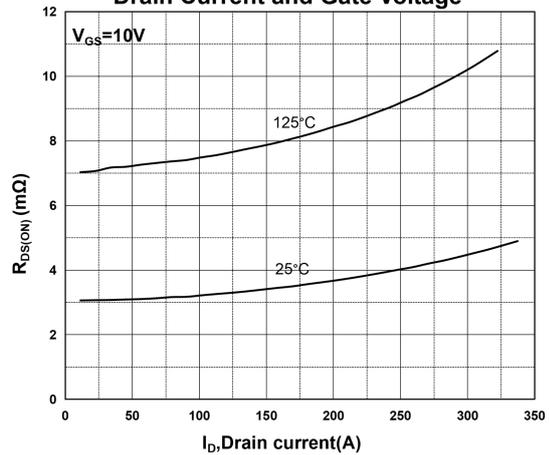
Transfer Characteristics



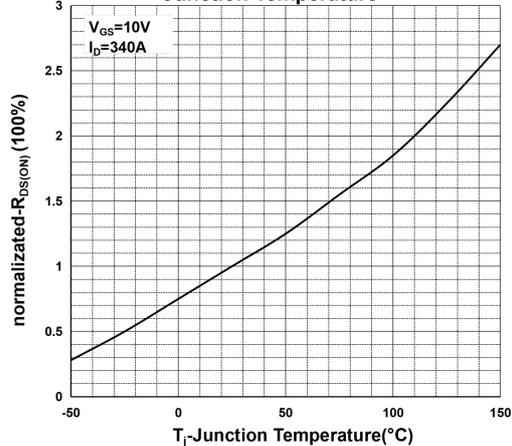
Transconductance



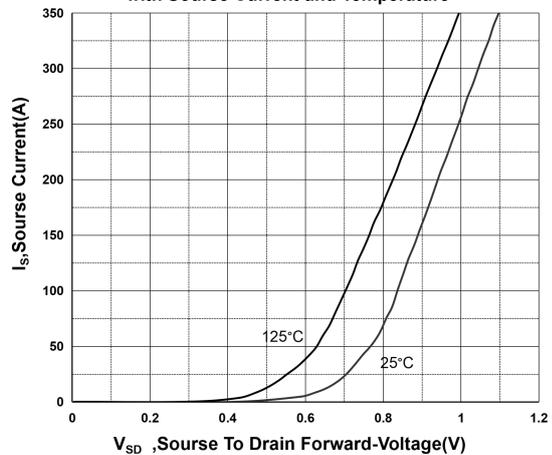
On-Resistance Variation vs Drain Current and Gate Voltage

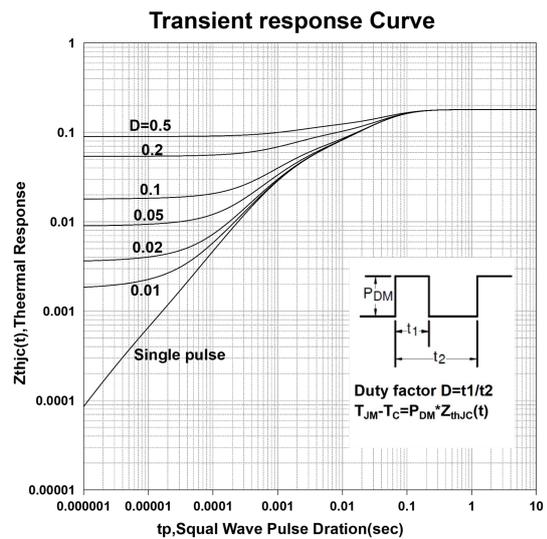
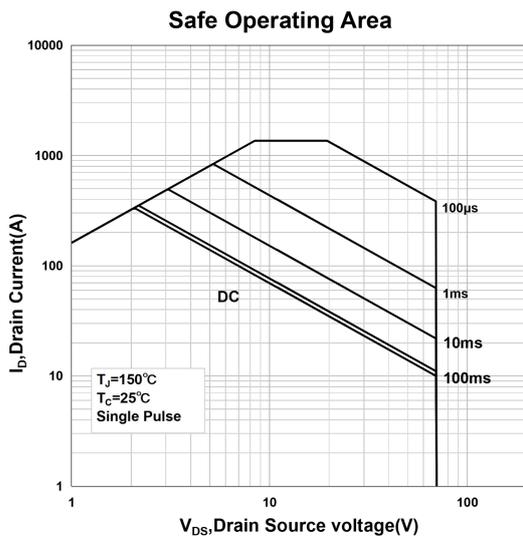
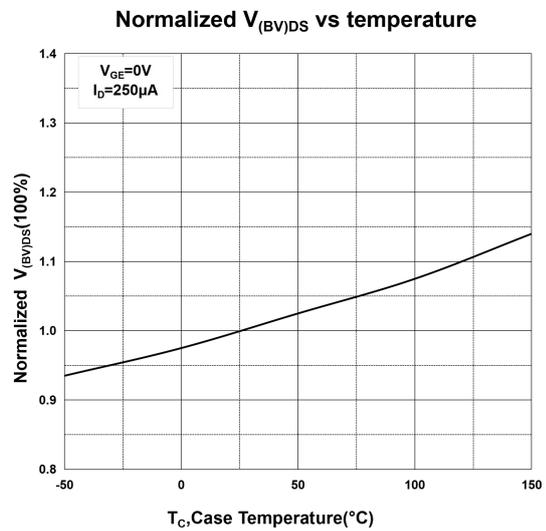
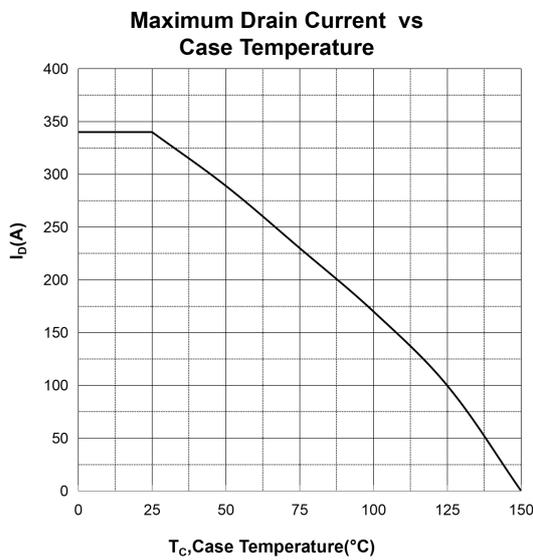
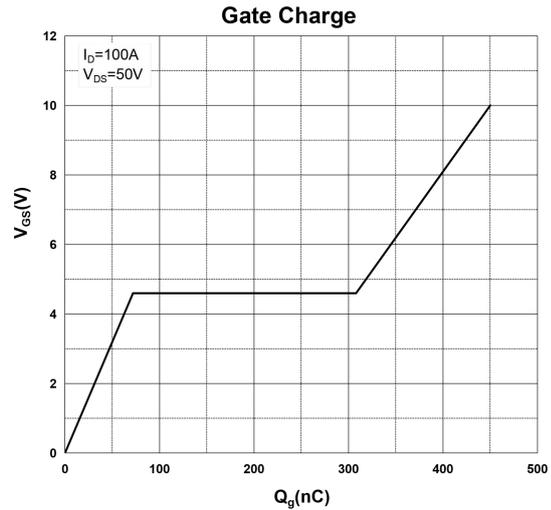
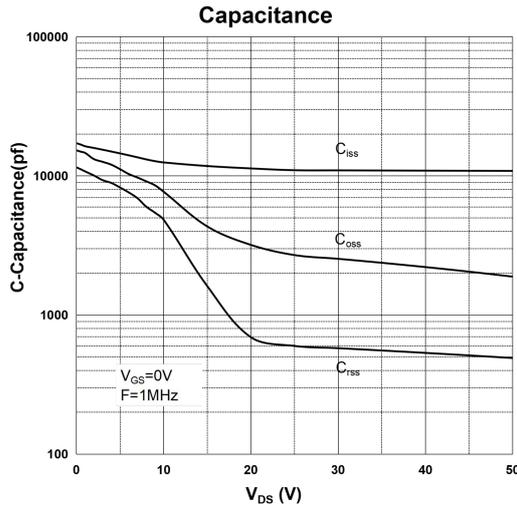


Normalized On-Resistance Variation vs Junction Temperature

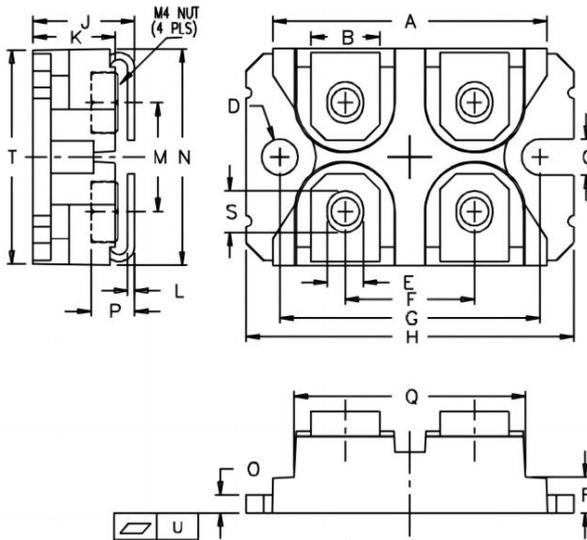


Body Diode Forward Voltage Variation with Source Current and Temperature





Package Mechanical DATA



Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	31.50	31.88	1.240	1.255
B	7.80	8.20	0.307	0.323
C	4.09	4.29	0.161	0.169
D	4.09	4.29	0.161	0.169
E	4.09	4.29	0.161	0.169
F	14.91	15.11	0.587	0.595
G	30.12	30.30	1.186	1.193
H	38.00	38.23	1.496	1.505
J	11.68	12.22	0.460	0.481
K	8.92	9.60	0.351	0.378
L	0.76	0.84	0.030	0.033
M	12.60	12.85	0.496	0.506
N	25.15	25.42	0.990	1.001
O	1.98	2.13	0.078	0.084
P	4.95	5.97	0.195	0.235
Q	26.54	26.90	1.045	1.059
R	3.94	4.42	0.155	0.174
S	4.72	4.85	0.186	0.191
T	24.59	25.07	0.968	0.987
U	-0.05	0.1	-0.002	0.004